

Issue Date: Jan. 12, 2024

MR7930/MR793200

UHF band RFID Sensor LSI

OVERVIEW

MR7930/MR793200 is a passive UHF band RFID Sensor LSI for the battery-less short-range IoT devices.

This LSI is equipped with sensor function to measure electrostatic capacitance.

It is possible to control sensor function by the mandatory command (*READ*, *WRITE*) from Reader/Writer (RW; interrogator) that is compliant with the international standard EPC global Generation2-Ver.2.0.1 (EPC standard or EPC Gen2). MR7930 is bump wafer product for inlay tag. MR793200 is package product that has SPI slave interface.

FEATURES

• RF communication

- Carrier frequency : 860 to 960 MHz (UHF band)

- Data transfer speed

RW => Tag : 26.7 to 128 kbps (when the values of data-0 and data-1 are the same)

Tag \Rightarrow RW : 40 to 640 kbps

- Modulation : DSB-ASK, SSB-ASK, PR-ASK

- Option command : ACCESS and BLOCK WRITE (data length is one or two words)

• RF communication characteristics

- Receiver sensitivity (passive)

 $\begin{array}{ccc} READ & : -9.5 \text{ dBm (LSI end)} \\ WRITE & : -8.5 \text{ dBm (LSI end)} \\ READ/WRITE (Sensor) & : -8.5 \text{ dBm (LSI end)} \\ - \text{Reflection coefficient} & : 0.7 \text{ (ASK transmission)} \end{array}$

Memory

EPC : 96 bits
USER : 144 bits
NVM rewrite time : 8ms (16 bits)
NVM write endurance : 10,000 cycles
NVM data retention : 10 years

Capacitive sensor

- Mesurement function : Range Max. 100pF

- Comparison function : Threshold Max. ±1.0pF (Low Range Mode only)

- Contorol command : Mandatory command (*READ*, *WRITE*)





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SPI interface (SPI Slave)

- Operating frequency : Max. 5 MHz - SPI type : 0 or 3

• Interrupt function : It is possible to receive the interrupt notification such as a read request and a write

completion from RW to host MCU.

Arbitration fuction : It is possible to avoid the collision of access from RW and MCU.

Shipment

Product name	Shipment	MCU interface	Remark
MR7930-11KDVWJ	Bump wafer		Passive
MR793200GD	24pin plastic WQFN	SPI	Passive/Semi-passive

Guaranteed operation range

- Operating temperature (ambient) : Ta = -40 to 65 $^{\circ}$ C - Operating voltage : $V_{DD} = 1.8$ to 3.6 V

Application

Short-range IoT sensor devices

- Battery-less sennsing system
- Periodic inspection system
- Logistics warehouse management system
- Maintenance and management systems for Infrastructure, Plants, and Buildings

BLOCK DIAGRAM

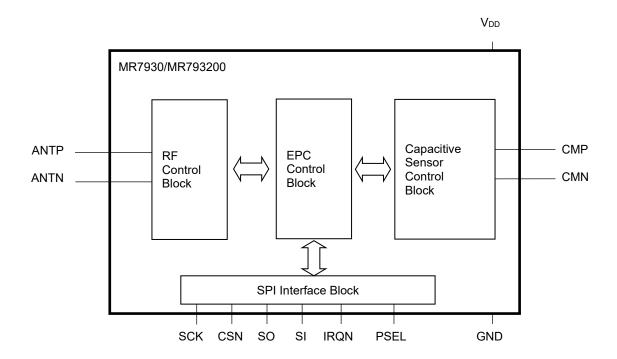


Figure 1 Block Diagram

PIN DESCRIPTION (MR7930)

MR7930 has the 4pads with bumps.

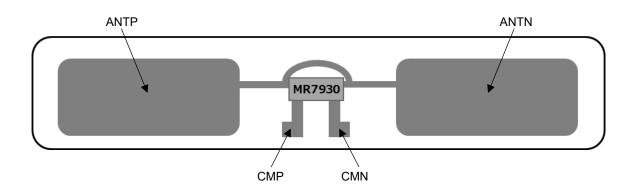


Figure 2 Inlay Image

Table 1 Pin List

Pin name	Description
ANTP	Antenna +pin
ANTN	Antenna -pin
CMP	Capacitive measurement +pin
CMN	Capacitive measurement —pin

PIN ASSIGNMENT (MR793200)

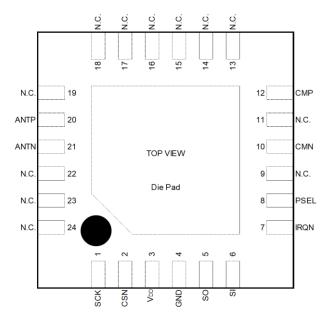


Figure 3 24pin WQFN

PIN DESCRIPTION (MR793200)

Table 2 Pin List (MR793200)

Pin				Terminal co	onnection	Initial state	e (V _{DD} = on)	
No.	Pin name	I/O	Description	SPI not used (Passive)	SPI used	PSEL = L	PSEL = H	Active level
1	SCK	I	Clock input	Open	Host IF	I-Disable	I-Z	_
2	CSN	I	Chip select input	Open	Host IF	I-Disable	I-Z	L
3	V_{DD}	PI	External power supply	Open	V_{DD}	_	_	_
4	GND	PI	Ground	Open	GND	_	_	_
5	SO	Ю	Data output	Open	Host IF	O-Z	O-L	_
6	SI	I	Data input	Open	Host IF	I-Disable	I-Z	_
7	IRQN	0	Interrupt output	Open	Host IF	O-H	O-H	L
8	PSEL	I	External power supply select input ("L" level: RF reception power supply, "H" level: External power supply)	Open	Host IF	-	I	н
9	N.C.	_	Open	Open	Open	_	_	_
10	CMN	Α	Capacitive measurement —pin	connection	connection	O-L	O-L	I-A
11	N.C.	_	Open	Open	Open	_	_	_
12	CMP	Α	Capacitive measurement +pin	connection	connection	O-L	O-L	I-A
13	N.C.	_	Open	Open	Open	_	_	_
14	N.C.	_	Open	Open	Open	_	_	_
15	N.C.	_	Open	Open	Open	_	_	_
16	N.C.	_	Open	Open	Open	_	_	_
17	N.C.	_	Open	Open	Open	_	_	_
18	N.C.	_	Open	Open	Open	_	_	_
19	N.C.	_	Open	Open	Open	_	_	_
20	ANTP	Α	Antenna +pin	Antenna +	Antenna +	I-A	I-A	I-A
21	ANTN	Α	Antenna -pin	Antenna -	Antenna -	I-A	I-A	I-A
22	N.C.	_	Open	Open	Open	_	_	_
23	N.C.	_	Open	Open	Open	_	_	_
24	N.C.	_	Open	Open	Open	_	_	_
_	Die Pad	_	Backside ground	Open	GND	_	_	_

Die Pad | - | Backside ground | Open | GND | I: Input pin, O: Output pin, IO: Input/output pin, A: Analog pin, PI: Power Input Open: Be sure to keep it open.

O-Z: High-impedance output, O-H: CMOS-H output, O-L: CMOS-L output, I-Disable: Input OFF

I-Z: High impedance input, I-A: Analog input

ELECTRILCAL CHARACTERISTICS

Absolute Maximum Ratings

Item	Symbol	Condition	Rating	Unit
Antenna Input Voltage	V_{max}	ANTP, ANTN	+2.0	V
Digital Input Current	I _{DI}	_	-1 to +1	mA
Digital Output Current	I _{DO}	_	-1 to +1	mA
Antenna Input Power	P _{AB}	_	+10	dBm
Storage Temperature	T _{stg}	_	-40 to +125	°C

● Absolute Maximum Ratings (MR793200)

Item	Symbol	Condition	Rating	Unit
Supply Voltage	V_{DD}	V _{DD} Pin	-0.3 to +4.6	V
Input Voltage	V _{DIN}	_	-0.3 to V _{DD} +0.3	V
Output Voltage	V_{DO}	_	-0.3 to V _{DD} +0.3	V

Recommended Operating Conditions

Item		Symbol	Condition	Min.	Тур.	Max.	Unit
Operating Temperature		Та	_	-40	+25	+65	°C
	Operating Frequency	F _{RF}	According to the radio law of each country	860	-	960	MHz
	Modulation Depth	(A-B) / A	_	80	90	100	%
RF	Reception Bit Rate	F _{rx}	When the value of data-0 and data-1 are same	26.7	_	128	kbps
	Power-up Rise Time	Tr	_	1	_	500	μs
	Power-up Stabilizing Time	Ts	_	_	_	1,500	μs
	Power-down Fall Time	Tf	_	1	_	500	μs

Recommended Operating Conditions (MR793200)

	Item	Symbol	Condition	Min.	Тур.	Max.	Unit
SPI	Supply Voltage	V_{DD}	_	1.8	3.0	3.6	V

NVM Characteristics

Ta = 25°C

					10	
Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Write Endurance	CYCew	_	_	10,000	-	Сус
Data Retention	T _{rtn}	_	_	10	_	Year
Write Time	Tew	1 word = 16 bit	_	7.0	8.0	ms

RF Communication Characteristics

Ta = 25°C

Item		Symbol	Condition	Min.	Тур.	Max.	Unit
Passive Sensitivity	READ Command	P _{R_R}	Tari = 25µs, PW = 0.4Tari, RTcal = 3Tari,	_	-9.5	_	dBm
	WRITE Command	P _{R_W}	TRcal = 2.6RTcal, DR = 8, Miller4, BLF = 41kbps, DSB-ASK.	-	-8.5	ı	dBm
	SENSOR Command	P _{R_S}	Modulation depth = 90%, PSEL = open or L ※at LSI end	1	-8.5	ı	dBm
	READ Command	P _{RS_R}	Tari = 25µs, PW = 0.4Tari, RTcal = 3Tari, TRcal = 2.6RTcal,	I	-20	ı	dBm
Semi-passive Sensitivity	WRITE Command	P _{RS_W}	DR = 8, Miller4, BLF = 41kbps, DSB-ASK,	ı	-20	-	dBm
	SENSOR Command	P _{RS_} s	Modulation depth = 90%, PSEL = H, V _{DD} = 3.0V **at LSI end	-	-20	-	dBm
Maximum Input Pow	er Supply	P _{MAX}	_	-	5	_	dBm
Antenna Input Impedance		Ср	Input power = -10dBm	_	2	_	pF
		Rp	Input frequency = 920MHz Xat LSI end on wafer	_	1	_	kΩ
Tag => RW Link Frequency		LF	_	40	_	640	kHz
Tag => RW Link Frequency Tole	rance	FT	_	0	_	±22	%

Capacitive Sensor Characteristics

Ta = 25°C

Item		Symbol	Condition	Min.	Тур.	Max.	Unit
	Range	_	_	5	_	25	pF
Low Range Mode	Resolution	_	_	_	0.01	_	pF
	Accuracy	_	_	_	5	_	%
	Range	_	_	15	_	100	pF
High Range Mode	Resolution	_	_	0.02	_	0.20	pF
	Accuracy	_	_	_	5	_	%
Comparison Function: Threshold (Low Range Mode Only)		_	_	_	_	±1.0	pF

● DC Characteristics (MR793200)

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
High Level Input Voltage (CSN, SCK, SI, PSEL)	V _{IH}	_	V _{DD} × 0.7	ı	V_{DD}	V
Low Level Low Voltage (CSN, SCK, SI, PSEL)	VIL	_	0	-	V _{DD} × 0.2	V
High Level Output Voltage (SO, IRQN)	Vон	IOH = -1mA	V _{DD} -0.6	1	1	V
Low Level Output Voltage (SO, IRQN)	VoL	IOL = 1mA	_	-	0.4	V
High Level Leakage (CSN, SCK, SI, SO)	IIH IOZH	$V_{IH} = V_{DD}$ or $V_{OH} = V_{DD}$	_	ı	1.0	μΑ
Low Level Leakage (CSN, SCK, SI, SO)	IIL IOZL	$V_{IL} = GND$ or $V_{OL} = GND$	-1.0	1	1	μA
Pin Capacitance	Cin	Input pin	_	5		pF
ғіп Сараспапсе	Co	Output pin	_	5	_	pF

Current Consumption

Ta = 25°C

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Stand-by 1 (V _{DD})	I _{DS1}	$PSEL = L, V_{DD} = 3.0V, RF off$	_	0.05	_	μΑ
Stand-by 2 (V _{DD})	I _{DS2}	PSEL = H, V _{DD} = 3.0V, RF off	_	14	ı	μΑ
Operation (V _{DD})	I _{DO}	PSEL = H, V _{DD} = 3.0V, RF off, SPI Slave 5.0MHz	_	52	ı	μΑ

● AC Characteristics (SPI Slave Interface, MR793200)

		V	$I_{DD} = 1.8 \text{ tc}$	3.6V, Loa	d capacity =	= 10 pF
Item	Symbol	Condition	Min.	Тур.	Max.	Unit
SCK Frequency	f _{SCK}	ı	0.39	_	5.0	MHz
SCK High Time	tsckwh	1	80	_	-	ns
SCK Low Time	tsckwl	_	80	_	_	ns
CSN High Time	tcs	_	600	_	_	ns
CSN Setup Time	t _{CSS}	_	200	_	_	ns
CSN Setup Time	tсsн		200	_	_	ns
SI Setup Time	tois		50	-	-	ns
SI Hold Time	t _{DIH}		50	_	_	ns
SO Output Delay Time	t _{PD1}	_	_	_	60	ns
SO Output Hold Time	tон	_	0	_	_	ns

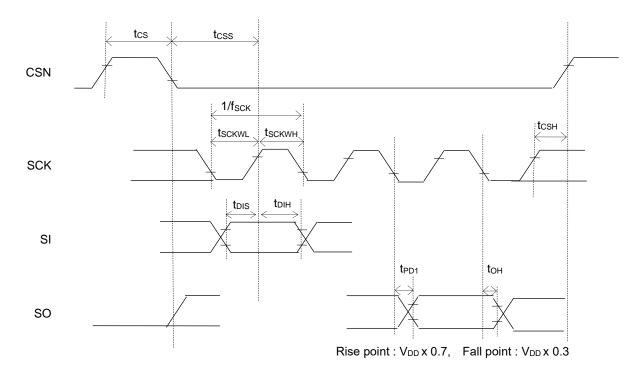


Figure 4 Input / Output and Setup / Hold timing

• External Power Supply Control: When Power-on (SPI Slave Interface, MR793200)

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
V _{DD} Power Rise time ※	T _{VS}	$V_{DD} = 1.8V$	0.05	ı	200	ms
V _{DD} -PSEL Setup Time	T _{PVS}	_	0	ı	ı	ns
V _{DD} -PSEL Hold Time	T _{PVH}	_	0	-	-	ns
PSEL-CSN Setup Time	Twlg	_	2	ı	ı	ms

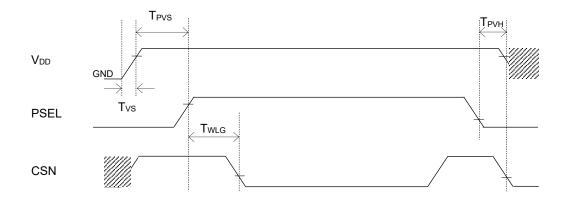


Figure 5 Power-on Sequence

&Set V_{DD} to 1.8V or higher starting from GND (= 0V) level. For other provisions, refer to the user's manual.

MEMOERY MAP

In compliance with the EPC standard, MR7930/MR793200's Memory consists of four banks: Reserved, EPC, TID, and USER. The USER bank consists of a non-volatile memory "NVM" and a volatile memory "RAM". It is possible to control the capacitive sensor functions by accessing "Capacitor monitor1" and "Capacitor monitor2" with *READ* or *WRITE* command.

Also, MR793200 has the SPI slave interface. It is possible to communicate between the host MCU and RW. However, RF (EPC) and SPI have different addresses, so be careful.

The address of RF communication from RW assigns by the EPC column of Table 3.

The address of SPI communication from the host MCU assigns by the SPI column of Table 3.

In addition, MR793200 has a status register for access from the host MCU. For details, refer to the user's manual.

Table 3 Memory Map

					I	able 3 Mem	ory iv	тар				
	EPC		SPI	Access	Size	Description		Description			Init	ial
N	1emBank	Addr	Addr *1	*2	(bit)		2000 гр. пост		Восоприон			
		h00	h4_00	R/W	32	Kill Password [31:16]		Kill Password [31:16]				
00	Reserved	h01	h4_02	R/W	32	ŀ	Kill Pa	assword [15:0]	h0000			
00	Reserved	h02	h4_04	R/W	32	Access Password [31:16]		h00	00			
		h03	h4_06	R/W	32	Access Password [15:0]		h00	00			
		h00	h0_0E	R	16		Store	edCRC [15:0]	_			
		h01	h4_08	R/W	16		Stor	redPC [15:0]	h340	0 *3		
		h02	h4_0A	R/W								
04	EDC.	h03	h4_0C	R/W								
01	EPC	h04	h4_0E	R/W	00	EPC *4						
		h05	h4_10	R/W	96			EPC		ŀ		
		h06	h4_12	R/W								
		h07	h4_14	R/W								
		h00	h4_16	R		Class ID [7:0] Mask designer ID [11:4]		hE2	83			
	h01					Mask			MR7930	h3805		
			h4_18	R		designer ID [3:0]	Ν	Nodel Number [11:0]	MR793200	h3806		
10	TID	h02	h4_1A	R	96	XTID [15:0]		h20				
		h03	h4_1C	R				D [47:32]				
		h04	h4_1E	R				D [31:16]	*5	5		
		h05	h4_20	R				ID [15:0]				
		h00	h4_22									
	USER	:	:	R/W	144		US	ER memory	h00	00		
	(NVM)	h08	h4_32									
		h09 h0A	h4_34 h4_36	R/W	32	Sensor mode setting		h0000_	_0000			
11		h3C	h6_22	R/W	16	RAM0 FLAG		h00	00			
		h42	h6_2E	R/W	16	RAM1 FLAG		h00	00			
	USER	h43	h6_30	R/W	16		Сара	citor monitor1	h42 . h40	S. 60000		
	(RAM)	h44	h6_32						h43 ~ h46 h47 ~ h78			
		:	:	R	-	Capacitor monitor2		h79 ~ h7E				
		h7B	h6_A0									

- *1: In the case of read access from SPI to an undefined address, read value is not fixed.
- *2: R (Read only), R/W (Read/Write) .
- *3: The initial value of StoredPC [15:0] is "b0011_0100_0000_0000".
 - UMI (StoredPC [10]) is fixed to "1". XI (StoredPC [9]) is fixed to "0".
- *4: At shipping test, a value as same as TID data is written in EPC data area.
- *5: ID [47:0] is Serial Number.

FUNCTION DESCRIPTIONS

MR7930/MR793200 is equipped with sensor function to measure electrostatic capacitance. Also, MR793200 has the SPI slave interface. It is possible to communicate between host MCU and RW. In this session, there are "Supported Command for RF communication", "Capacitive Sensor Functions (Measurement and Comparison)", "SPI Slave Interface", and "Arbitration Function".

Supported Commands for RF communication

MR7930/MR793200 supports all mandatory EPC standard commands and some of optional commands as shown in Table 4. It is possible to control sensor function by the mandatory command (*READ*, *WRITE*) from RW.

Table 4 Command List							
Classification	Command	Code (binary)					
	QUERYREP	b00					
	ACK	b01					
	QUERY	b1000					
	QUERYAJUST	b1001					
	SELECT	b1010					
Mandatory	NAK	b1100_0000					
	REQ_RN	b1100_0001					
	READ	b1100_0010					
	WRITE	b1100_0011					
	KILL	b1100_0100					
	LOCK	b1100_0101					
Ontional	ACCESS	b1100_0110					
Optional	BLOCKWRITE	b1100 0111					

Table 4 Command List

Capacitive Mesurement Function

MR7930/MR793200 can measure the electrostatic capacitance of the object connected to CMP pin and CMN pin. Capacitive measurement function has two modes. There are "Low Range" and "High Range" as shown in Table 5. It is possible to switch two modes by setting "Sensor mode setting" in the USER bank.

Mode	Resolution	Upper limit	Measurement time (RF communication)	Comparison function
Low Range	10 fF	25 pF	90 ms	support
High Range	20 ~ 200 fF	100 pF	(BLF = 41kbps)	no support

Table 5 Capacitive Measurement Mode

Also, it is possible to control the Capacitive Measurement function by accessing "Capacitor monitor2" with *READ* command. The result of Capacitive Measurement is a 12bits binary data. The calculation formula is different for the two modes.

Measurement time is the reference value between *READ* command and sensor data response. (BLF = 41 kbps; Miller4) For details, refer to the user's manual.

Capacitive Comparison Function

MR7930/MR793200 can compare the current capacitance value with the reference value. And it can detect increases and decreases. This function is Low range mode only.

The reference value and Threshold value (increase or decrease) are stored in "Sensor mode setting".

Also, it is possible to control the Capacitive Comparison function by accessing "Capacitor monitor2" with *READ* command.

The result of Capacitive Comparison function is an 1bit binary data. For details, refer to the user's manual.

SPI Slave Interface

When PSEL is "H" (Semi-passive mode), MR793200 can use SPI Slave Interface to communicate with the host MCU. As shown in Figure 6, connect the SPI pin (SCK, CSN, SO, SI, IRQN, PSEL) of MR793200 to the host MCU pin (Host IF). It is possible to communicate between host MCU and RW by using USER bank (USER memory, RAM0 FLAG, RAM1 FLAG).

Also, the host MCU can read and write status register of MR793200. For details, refer to the user's manual.

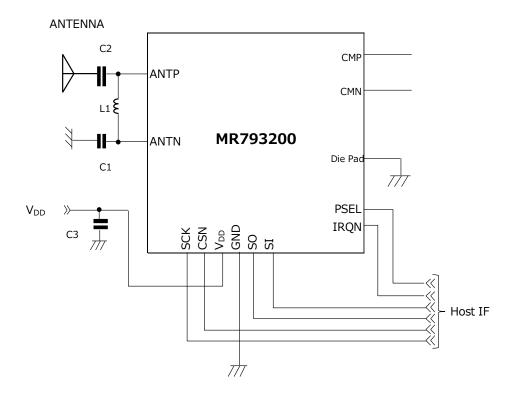


Figure 6 Connection Example with the Host MCU Interface

Communication Function Usage Conditions

As shown in Table 6, each setting (PSEL, VDD, MCU connection) determines which communication functions are available. For details on the sequence of each communication functions and interrupt factors, refer to the user's manual.

Table 6 Communication Function Usage Conditions

Usage conditions						Communication function		
Mode	PSEL	V_{DD}	MCU connection	Status		SPI	Interrupt	Product name
	Open	None	None No battery		Enabled	Disabled	Disabled	MR7930
passive	Open or "L" level	None	None	No battery or Low battery etc.	Enabled	Disabled	Disabled	
	"L" level	Supported	Supported	Waiting for an interrupt	Enabled	Disabled	Enabled	MR793200
Semi- passive	"H" level	Supported	Supported	SPI communication available	Enabled	Enabled	Enabled	

Arbitration Function

MR793200 has Arbitration function. It is possible to avoid the collision of access from RW and the host MCU. As shown in Table 7, SPI_EXCL setting constrains MR793200 Memory Bank's access. SPI_EXCL is a register bit in SPI_STAT (SPI Status Register), and initial value is "0". Also, MR793200's Registers can be set only from the host MCU.

In passive mode, MR7930/MR793200 responds only to RF communication from RW. SPI EXCL is "0".

In semi-passive mode, MR793200 responds to RF communication from RW and SPI communication from the host MCU. When SPI_EXCL is set to "0", it is possible to access memory except for writing to NVM area form the host MCU. If RW and the host MCU access MR793200 at the same time, RF communication will be executed first. When SPI_EXCL is set to "1", it is possible to access memory by only SPI communication from the host MCU. Therefore, MR793200 does not accept access from RW. For details, refer to the user's manual.

Table 7 Arbitration Function

		Command	SDI EVCI	Memory access					
Mode	V_{DD}	input	SPI_EXCL (register)	NVM area		RAM area			
		iliput	(register)	Read	Write	Read	Write		
Passive	None	RW (EPC)	0	Enabled	Enabled	Enabled	Enabled		
Semi-passive Supported	RW (EPC)	0	Enabled	Enabled	Enabled	Enabled			
	TAVV (ET C)	1	Non-response	Non-response	Non-response	Non-response			
	Supported		MCIT(SDI)	0	Enabled	Disabled	Enabled	Enabled	
		MCU (SPI)	1	Enabled	Enabled	Enabled	Enabled		

PAKAGE DIMENSIONS

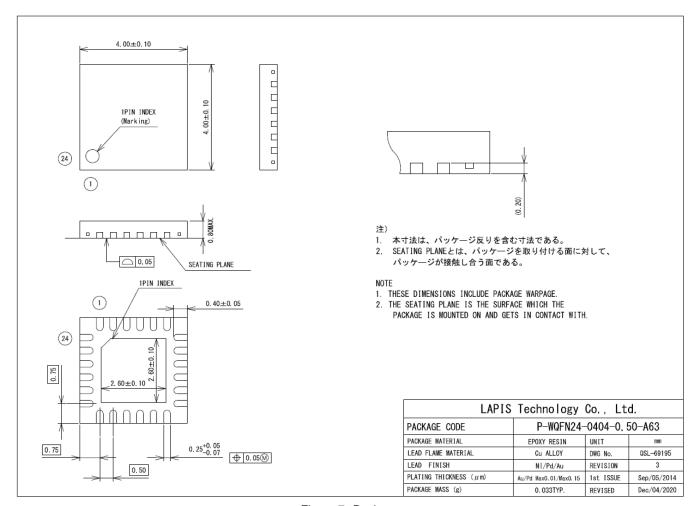


Figure 7 Package

ABBREVIATED TERMS

Item	Comment						
BLF	Backscatter-Link Frequency						
DR	Divide Ratio						
DSB-ASK	Double Side Band Amplitude Shift Keying						
EPC	Electronic Product Code						
EPC standard, EPC Gen2	EPCglobal Class1 Generation2(Ver.2.0.1)						
loT	nternet of Things						
MCU	Micro Controller Unit						
N.C.	Non-Connect						
NVM	Non-Volatile Memory						
PR-ASK	Phase Reversal Amplitude Shift Keying						
RAM	Random Access Memory						
RFID	Radio Frequency IDentification						
RW	Reader-Writer (interrogator)						
SPI	Serial Peripheral Interface						
SSB-ASK	Single Side Band Amplitude Shift Keying						
Tari	Type A Reference Interval						
TID	Tag ID						
UHF	Ultra High Frequency						

REVISION HISTORY

Decument No.	Date	Page		Description	
Document No.	Document No.	Date	Previous Edition	Current Edition	Description
FEDM7930-01	Jan. 16, 2023	_	_	1st Edition	
FEDM7930-02	Jan. 12, 2024	P.2	P.2	Product name update Added applications	
		P.18	P.18	•Updated Notes	

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